

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
650V	2.47Ω@10V	4A

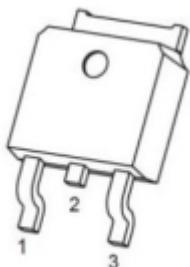
## Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

## Application

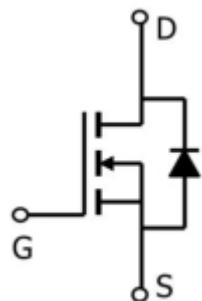
- DC-DC Converter
- Ideal for high-frequency switching and synchronous rectification

## Package

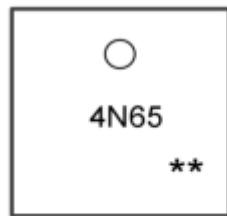


TO-252-2L(G:1 D:2 S:3)

## Circuit diagram



## Marking



**4N65**  
\*\*                    =Device Code  
                      =Week Code

## Absolute maximum ratings

( $T_a=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	650	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current <sup>1</sup> ( $T_c = 25^\circ\text{C}$ )	$I_D$	4	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	16	A
Single Pulse Avalanche Energy <sup>3</sup>	$E_{AS}$	163	mJ
Total Power Dissipation( $T_c = 25^\circ\text{C}$ )	$P_D$	77	W
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	1.62	$^\circ\text{C} / \text{W}$
Storage Temperature Range	$T_{STG}$	-55~ +150	$^\circ\text{C}$
Operating Junction Temperature Range	$T_J$	-55~ +150	$^\circ\text{C}$

## Electrical characteristics

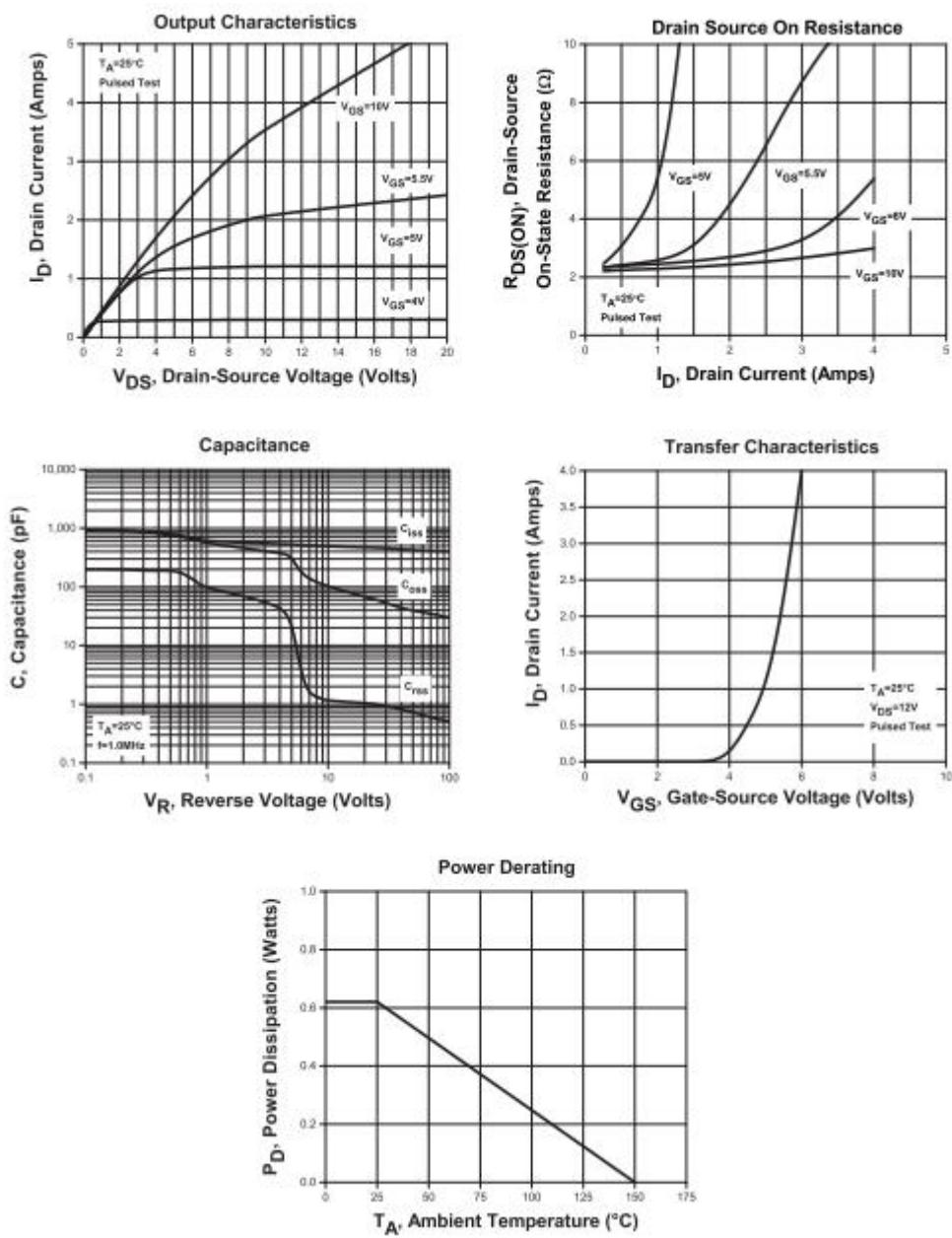
( $T_A=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$\text{V}_{\text{GS}} = 0\text{V}, \text{I}_D = 250\mu\text{A}$	650			V
Drain-Source Leakage Current	$\text{I}_{\text{DSS}}$	$\text{V}_{\text{DS}} = 650\text{V}, \text{V}_{\text{GS}} = 0\text{V}$ $T_J = 25^\circ\text{C}$			1	$\mu\text{A}$
Gate-Source Leakage Current	$\text{I}_{\text{GSS}}$	$\text{V}_{\text{GS}} = \pm 30\text{V}, \text{V}_{\text{DS}} = 0\text{V}$			$\pm 100$	$\mu\text{A}$
Gate threshold voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}, \text{I}_D = 250\mu\text{A}$	2	3.2	4	V
Static Drain-Source on-Resistance	$\text{R}_{\text{DS(on)}}$	$\text{V}_{\text{GS}} = 10\text{V}, \text{I}_D = 2\text{A}$		2.47	3	$\Omega$
<b>Dynamic characteristics</b>						
Input Capacitance	$\text{C}_{\text{iss}}$	$\text{V}_{\text{DS}} = 25\text{V}, \text{V}_{\text{GS}} = 0\text{V},$ $f = 1\text{MHz}$		460		pF
Output Capacitance	$\text{C}_{\text{oss}}$			63		
Reverse Transfer Capacitance	$\text{C}_{\text{rss}}$			1.2		
<b>Switching Characteristics</b>						
Total Gate Charge	$\text{Q}_g$	$\text{V}_{\text{DS}} = 520\text{V}, \text{V}_{\text{GS}} = 10\text{V},$ $\text{I}_D = 4\text{A}$		11		nC
Gate-Source Charge	$\text{Q}_{\text{gs}}$			3		
Gate-Drain Charge	$\text{Q}_{\text{gd}}$			5		
Turn-On Delay Time	$\text{T}_{\text{d(on)}}$	$\text{V}_{\text{DD}} = 325\text{V}, \text{V}_{\text{GS}} = 10\text{V},$ $\text{R}_G = 10\Omega, \text{I}_D = 4\text{A}$		9		nS
Rise Time	$\text{T}_r$			22		
Turn-Off Delay Time	$\text{T}_{\text{d(off)}}$			24		
Fall Time	$\text{T}_f$			21		

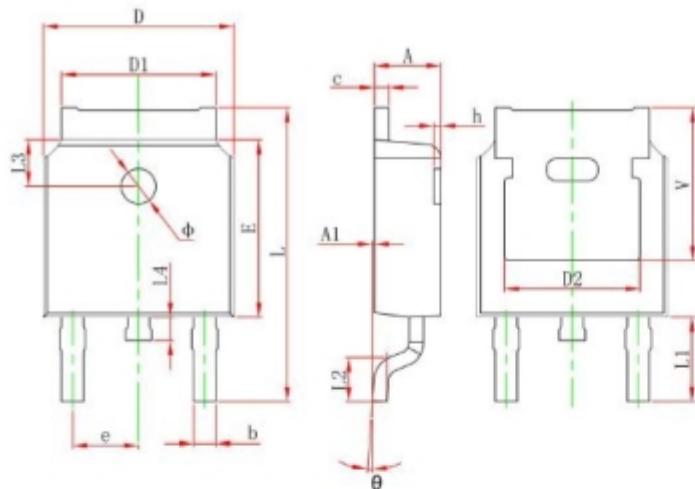
### Notes:

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $\text{ID}=5\text{A}, \text{L}=10\text{mH}$

## Typical Characteristics



## TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	